Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031 U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE ed to respond to a collection of information unless it contains a valid OMB control number. DEC 2 8 2004

	te for form 1449A/PTC		RADEMENT	Cor	mplete if Known
	RMATION D	ue Ci	PADE	Application Number	09/535,015
				Filing Date	March 24, 2000
STA	STATEMENT BY APPLICANT			First Named Inventor	Shunpei YAMAZAKI et al.
	(use as many sheets	as neces	ssary)	Group Art Unit	2811
				Examiner Name	S. Crane
Sheet	1	of	1	Attorney Docket Number	0756-2131

				U.S. PATENT DOCUMEN	TS	
Examiner Initials	Cite No.1			Name of Patentee or Applicant of	Date of Publication of Cited  Document  MM-DD-YYYY	Pages, Columns, Lines, Where Relavant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)	Cited Document	, , , , , , , , , , , , , , , , , , ,	
SWL		5,531,862		Otsubo et al.	07/02/1996	
1		5,575,883		Nishikawa	11/19/1996	
		5,704,986		Chen et al.	01/06/1998	
		5,902,993		Okushiba et al.	05/11/1999	
<del></del>		5,970,327		Makita et al.	10/19/1999	
		6,006,763		Mori et al.	12/28/1999	•
		6,162,704		Yamazaki et al.	12/19/2000	
		6,177,302		Yamazaki et al.	01/23/2001	
1		6,294,441		Yamazaki	09/25/2001	
		6,461,943		Yamazaki et al.	10/08/2002	
		6,465,287		Yamazaki et al.	10/15/2002	
	<u> </u>	6,495,404		Teramoto et al.	12/17/2002	
1		6,528,358		Yamazaki et al.	03/04/2003	
SWC		6,620,711		Yamazaki	09/16/2003	

			F	DREIGN PATENT DOC	UMENTS		
Examiner Initials	Cite No.1	f	Foreign Patent Document	Name of Patentee or	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
***************************************		Office <sup>3</sup>	Kind Code <sup>a</sup> Number <sup>4</sup> (if known)	Applicant of Cited Document			Τ <sup>4</sup>
SWC	<del> </del>	JP	08-045839		02/16/1996		Abst.
000		JP	08-045840		02/16/1996		Abst.
SWC		JP	08-097169		04/12/1996		Abst.
	<del> </del>				<del> </del>		
	ļ						ļ
		l	li	l			L

Examiner Signature	CRANE	Date Considered	5/200	

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

tment of Commerce Serial No. 09/535,015 Form PTO-1449 Atty Docket 0756-2131 Petent and Trademark Office (Rev. 8-83) Applicants: Shupei YAMAZAKI et al. INFORMATION DISCLOSURE STATEMENT Group Art Unit: 2825 Filing Date: March 24, 2000 U.S. PATENT DOCUMENTS Filing Date Class Subclass Date Document Number Examiner (if appropriate) Initial Schimmer 06/18/1968 3,389,024 SU Sandera 01/01/1974 3,783,049 Fan et al. 11/22/1977 4,059,461 01/10/1978 Reuschel 4,068,020 Cuomo et al. 01/02/1979 4,132,571 11/13/1979 Flatley 4,174,217 Ovshinsky et al. 10/07/1980 4,226,898 11/04/1980 Schmidt 4,231,809 06/02/1981 **Ipri** 4,271,422 07/14/1981 Hsu 4,277,884 11/17/1981 Chang 4,300,989 Shibata 01/05/1982 4,309,224 05/25/1982 Risch et al. 4,331,709 Glaeser et al. 04/05/1983 4,379,020 Tasch, Jr. et al. 10/18/1983 4,409,724 09/18/1984 Sirinyan et al. 4,472,458 11/06/1984 Barthel 4,481,121 Mori et al. 08/13/1985 4,534,820 10/01/1985 Gibbons 4,544,418 Nakata et al. 10/08/1985 4,546,376 07/01/1986 **Ipri** 4,597,160 Swartz et al. 01/06/1987 4,634,473 04/05/1988 Yamabe et al. 4,735,824 Faraone 07/05/1988 4,755,481 Fox et al. 03/27/1990 4.911,781 Moser et al. 09/25/1990 4,959,247 Yamazaki 09/25/1990 4,959,700 02/26/1991 Moslehi et al. 4,996,077 Bell et al. 02/26/1991 4,996,523 Jaccodine et al. 08/27/1991 5,043,224 Moran 12/24/1991 5,075,259 لكلأ 700 Date Considered <u>Examiner</u> \*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this formwith next communication to applicant.

U.S.D., artment of Commerce Serial No. 09/535.015 Form PTO-1449 Atty Docket 0756-2131 Patent and Trademark Office (Rev. 8-83) Applicants: Shupei YAMAZAKI et al. INFORMATION DISCLOSURE STATEMENT Filing Date: March 24, 2000 Group Art Unit: 2825 U.S. PATENT DOCUMENTS Filing Date Class Subclass Date Name **Document Number** Examiner (if appropriate) Initial 02/18/1992 Moslehi 5,089,441 Mitra et al. 05/12/1992 5,112,764 Sameshima et al. 09/08/1992 5,145,808 Liu et al. 09/15/1992 5,147,826 12/22/1992 Asakawa et al. 5,173,446 Nakamura et al. 04/06/1993 5,200,630 06/22/1993 Sugino et al. 5,221,423 07/06/1993 Sugino et al. 5,225,355 Lim 09/14/1993 5,244,836 Tran 10/19/1993 5,254,480 Yamazaki et al. 11/16/1993 5,262,350 Yamazaki 11/16/1993 5,262,654 01/04/1994 Fonash et al. 5,275,851 Yonehara 01/11/1994 5.278,093 Yamazaki et al. 02/22/1994 5,289,030 03/22/1994 Yamazaki et al. 5,296,405 Lagendijk et al. 03/29/1994 5,298,075 Yamazaki et al. 05/03/1994 5,308,998 05/17/1994 Zhang et al. 5,313,075 Zhang et al. 10/04/1994 5,352,291 Oostra et al. 10/11/1994 5,354,697 10/25/1994 Wong 5,358,907 11/22/1994 Mei et al. 5,366,926 Doyle et al. 5,387,530 02/07/1995 06/13/1995 Wakai 5,424,230 11/28/1995 Hamada 5,470,763 Chiang et al. 5,480,811 01/02/1996 04/02/1996 Miyasaka et al. 5,504,019 Horai et al. 04/16/1996 5.508,207 Yonehara et al. 06/25/1996 5,530,266 Yonehara · 07/02/1996 5,531,182 Date Considered Examiner \*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if

not in conformance and not considered. Include copy of this formwith next communication to applicant.

U.S.L. .rtment of Commerce Form PTO-1449 Atty Docket 0756-2131 Serial No. 09/535,015 Patent and Trademark Office (Rev. 8-83) Applicants: Shupei YAMAZAKI et al. INFORMATION DISCLOSURE STATEMENT Filing Date: March 24, 2000 Group Art Unit: 2825 U.S. PATENT DOCUMENTS Filing Date Class Subclass Date **Document Number** Examiner (if appropriate) Initial Funai et al. 08/27/1996 5,550,070 Hsu et al. 12/03/1996 5,580,815 04/08/1997 Makita et al. 5,619,044 08/26/1997 Takemura et al. 5,661,311 11/04/1997 Hwang 5,684,317 Tang et al. 11/04/1997 5,684,365 Yamazaki et al. 12/02/1997 5,693,541 12/02/1997 Inoue et al. 5,693,959 Makita et al. 12/09/1997 5,696,003 02/10/1998 Zhang 5,717,224 03/31/1998 Chang et al. 5,734,179 07/28/1998 Takayama et al. 5,786,796 Kousai et al. 08/18/1998 5,795,795 Mitanaga et al. 09/15/1998 5.808,321 10/13/1998 Arai et al. 5,821,560 Takemura 10/27/1998 5,828,429 11/17/1998 Sugawara 5,838,508 12/01/1998 Takayama et al. 5,843,225 12/08/1998 Ju 5,846,857 03/16/1999 Zhang et al. 5.882,960 03/30/1999 Yamazaki et al. 5,888,858 Zhang et al. 04/20/1999 5,895,933 05/04/1999 Yamazaki et al. 5.899,547 07/27/1999 Yamazaki et al. 5,929,464 Yamazaki et al. 5,933,205 08/03/1999 08/17/1999 Zhang 5,940,732 10/05/1999 Yamazaki et al. 5,962,869 Yamazaki et al. 5,963,278 10/05/1999 Yamazaki et al. 11/16/1999 5,985,740 11/23/1999 Zhang 5,990,491 Yamazaki 5,990,542 11/23/1999 Date Considered **Examiner** \*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this formwith next communication to applicant.

U.S.L. intment of Commerce Serial No. 09/535,015 Atty Docket 0756-2131 Form PTO-1449 Patent and Trademark Office (Rev. 8-83) Applicants: Shupei YAMAZAKI et al. INFORMATION DISCLOSURE STATEMENT Group Art Unit: 2825 Filing Date: March 24, 2000 U.S. PATENT DOCUMENTS Filing Date Subclass Name Class Date **Document Number** Examiner (if appropriate) Initial 12/21/1999 Zhang et al. 6,005,648 01/04/2000 Yamazaki 6,011,277 01/11/2000 Ohtani 6,013,929 Yamazaki et al. 04/11/2000 6,048,758 05/16/2000 Ohtani 6,063,654 Yamazaki et al. 06/20/2000 6,077,731 Yamazaki et al. 07/25/2000 6.093,934 Yamazaki et al. 08/08/2000 6,100,562 Mayer 04/08/1975 RE 28,385 Heiman et al. 04/08/1975 RE 28,386 FOREIGN PATENT DOCUMENTS Class Subclass **Translation** Country Date **Document Number** Examiner Yes Initial Engl. 10/09/1984 FΡ 0 178 447 Full 07/27/1989 Japan 01-187814 Abst. 07/27/1989 Japan 01-187874 Abst. 07/27/1989 Japan 01-187875 Abst. 08/18/1989 Japan 01-206632 Full 05/30/1990 Japan 02-140915 Abst. 06/07/1990 Japan 02-148687 Abst. 11/09/1990 Japan 02-275641 Abst. 12/11/1991 Japan 03-280418 Full 12/11/1991 03-280420 Japan Abst. 04/02/1993 Japan 05-082442 Abst. 04/30/1993 Japan 05-107561 Abst. 11/12/1993 05-299348 Japan Full 08/19/1994 Japan 06-232059 Abst. 06/23/1995 07-161634 Japan Abst. 12/08/1995 Japan 07-321339 Abst. 05/21/1996 Japan 08-129358 Abst. 05/21/1996 Japan 08-129359 Date Considered Examiner \*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this formwith next communication to applicant.

U.S.L \_ artment of Commerce Form PTO-1449 Serial No. 09/535,015 Atty Docket 0756-2131 Patent and Trademark Office (Rev. 8-83) Applicants: Shupei YAMAZAKI et al. INFORMATION DISCLOSURE STATEMENT Filing Date: March 24, 2000 Group Art Unit: 2825 FOREIGN PATENT DOCUMENTS Country Class Subclass <u>Translation</u> Document Number Examiner Yes Initial Abst. 05/21/1996 Japan 08-129360 Abst. 09/13/1996 08-234683 Japan Abst. 09/17/1996 Japan 08-241047 Abst. 09/17/1996 Japan 08-241048 Abst. 09/17/1996 Japan 08-241057 Abst. 09/17/1996 Japan 08-241997 Full 06/10/1985 60-105216 Japan Full 04/01/1986 Japan 61-063017 Abst. 04/01/1986 Japan 61-063107 Abst. 07/25/1987 Japan 62-169356 Abst. 03/27/1989 Japan 64-081324 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Examiner Initial Caune et al., "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact With Some Metals", January 1, 1989, pp. 597-604, Applied Surface Schience, Vol. 36 Stoemnos et al., "Crystallization of Amorphous Silicon By Reconstructive Transformation Utilizing Gold", March 18, 1991, pp. 1196-1198, Appl. Phys. Lett. 58(11) Kakkad et al., "Crystallized Si-Films By Low-Temperature Rapid Thermal Annealing of Amorphous Silicon", March 1, 1989, pp. 2069-2072, J. Appl. Phys. 65(5) Oki et al., "Effect of Deposited Metals On the Crystallization Temperature of Amorphous Germanium Film", 1969, pp. 1056, Jpn. J. Appl. Phys. 8 Kuznetsov et al., "Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting From Ion Implantation and Annealing", 1993, pp. 990-993, Nucl. Instruments Methods Physics Research, 880/881 Takenaka et al., "High Mobility Poly-Si Thin Film Transistors Using Solid Phase Crystallized a-Si Films Deposited by Plasma Enhanced Chemical Vapor Deposition", December 1990, pp. L2380-L2383, Jpn. J. Appl. Phys. Vol. 29, No. 12 Hatalis et al., "High Performance Thin-Film Transistors in Low Temperature Crystallized LPCVD Amorphous Silicon Films", August 1987, pp. 361-364, Elec. Dev. Letters Vol. EDL 8, No. 8 Zorabedian et al., "Lateral Seeding of Silicon-on-Insulator Using an Ellipitical Laser Beam: A Comparison of Scanning Methods", 1984, pp. 81-86, Mat. Res. Soc. Symp. Proc. Vol. 33 Spaepen et al., "Metal-Enhanced Growth of Silicon", 1992, pp. 483-499, Crucial Issues in Semiconductor Materials & Processing Technologies Green et al., "Method To Purify Semiconductor Wafers", October 1973, pp. 1612-1613, IBM Tech. Discl. Bulletin Vol. 16, \W( Date Considered Examiner \*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this formwith next communication to applicant.

U.S.D. ...tment of Commerce Form PTO-1449 Serial No. 09/535.015 Atty Docket 0756-2131 Patent and Trademark Office (Rev. 8-83) Applicants: Shupei YAMAZAKI et al. INFORMATION DISCLOSURE STATEMENT Group Art Unit: 2825 Filing Date: March 24, 2000 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Examiner Initial Boyd et al., "Oxidation of Silicon Surfaces by CO2 Lasers", July 15, 1982, pp. 162-164, Applied Phys. Letters, Vol. 41, No. SUL Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology", 1986, pp. 215-216, Lattice Press Lau et al., "Solid Phase Epitaxy in Silicide Forming System", 1977, pp. 313-322, Thin Solid Films, 47 Kawazu et al., "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation", December 1990, pp. 2698-2704, Inst. of Appl. Phys. Vol. 29, No. 12 Wolf et al., "Silicon Processing for the VLSI Era Volume 1 - Process Technology", 1986, pp. 550-551, Lattice Press Bruines et al., "Between Explosive Crystallization and Amorphous Regrowth: Inhomogeneous Solidification Upon Pulsed Laser Annealing of Amorphous Silicon", March 1, 1987, pp. 507-509, Applied Physics Letter, Vol. 50 Kawazu et al., "Initial Stage of the Interfacial Reaction beween Nickel and Hydrogenated Amorphous Silicon", April 1, 1990, pp. 729-738, Japanese Journal of Appl Phys., Vol. 29 Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon", 1989, pp. 66-68, Journal of Non-Crystaline Solids, 115 Suresh et al., "Electroless Plated Nickel Contacts to Hydrogenated Amorphous Silicon", January 1, 1994, pp. 78-81, Thin Solid Films, Vol. 252 Sakaguchi et al., "Current Progress in Epitaxial Layer Transfer", March 1, 1997, pp. 378-387, IEICE Trans. Electron, Vol E80 C/No. 3 Kouvatsos et al., "Fluorine-enhanced Oxidation of Polycrystalline Silicon and Application to Thin-Film Transistor Fabrication", August 24, 1992, pp. 937-939, Appl. Phys. Letter, Vol. 61, No. 8 Sze, "VLSI Technology", January 1, 1988, pp. 397-400, McGraw-Hill Publishing Company, Second Edition Ghandhi, "VLSI Fabrication Principles", January 1, 1983, pp. 419-429, Wiley and Sons Kuper et al., "Effects of Fluorine Implantation on the Kinetics of Dry Oxidation of Silicon", August 1, 1986, pp. 985-990, J. Applied Physics Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology", 1986, pp. 198-207, Lattice Press Hemple et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", 1993, pp. 921-924, Solid State Communications, Vol. 85, No. 11 Kuo, "Thin Film Transistor Technologies", Vol 94-35, pp 116-122, The Electrochemical Society Proceedings Author Unknown, "Thermo Auto-chrome Full Color Recording Technology", May 31, 1995, pp. Unknown, Technology Information Association Wolf et al., "Thermal Oxidation of Single Crystal Silicon", 1986, pp. 207-211, Silicon Processing for the VLSI Era Erokhin et al., "Spatially Confined Nickel Disilicide Formation at 400c on Ion Implantation Preamorphized Silicon", Dec 6, 1993, pp 3173-3175, Appl. Phys. Lett. 63 (23) Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR Batstone et al., "Microscopic Processes in Crystallisation", January 1, 1994, pp. 257-268, Solid State Phenomena, Vol 37-38 Cammarata et al., "Silicide Precipitation and Silicon Crystallization in Nickel Implanted Amorthous Silicon Thin Films". Susc Oct 10, 1990, pp. 2133-2138, J. Mater. Res. Vol. 5, No. 10 Date Considered Examiner. \*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this formwith next communication to applicant.

orm PTO-1449 U.S.L., itment of Commerce Rev. 8-83) Patent and Trademark Office		Serial No. 09/535,015
INFORMATION DISCLOSURE STATEMENT	Applicants: Shupei YAMAZAKI	l et al.
	Filing Date: March 24, 2000	Group Art Unit: 2825
OTHER DOCUMENTS	(Including Author, Title, Date, Pertinent F	Pages, Etc.)
miner al		
Hayzelden et al., "Silicide Formation and Silicide Media Films", May 15, 1993, pp. 8279-8289, J. Appl. Phys. 73	ited Crystallization of Nickel-Implan (12)	ted Amorphous Silicon Thin
Kuznetsov et al., "Silicide Precipitate Formation and So 5-8, 1993, pp. 191-194, Inst. Phys. Conf. Ser. No. 134.4	lid Phase Re-Growth of Ni-Implanted Proceedings of Royal Microscopic	d Amorphous Silicon", April al Society Conf.
Liu et al., "Polycrystalline Silicon Thin Film Transistors Low-Temperature Processing", May 17, 1993, pp. 2554	on Corning 7059 Glass Substrates U	
Liu et al., "Selective Area Crystallization of Amorphous August 14, 1989, pp. 660-662, Appl Phys. Lett 55(7)		Rapid Thermal Annealing",
August 14, 1763, pp. 000-002, 11pp.11a/st. 2011-35(17)		
	•	
	•	
		•
·		
•		
	•	•
		COPT
		COPY
Examiner CRANE	Date Considered	1,00×

09/08/2000

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Upder the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitu	te for form 1449A/PTC	)		Cor	nplete if Known
١٥٥	RMATION D	uec i	OCUPE	Application Number	09/535,015
				Filing Oate	March 24, 2000
SIA	TEMENT BY	APP	LICANI	First Named Inventor	Shunpei YAMAZAKI et al.
	(use as many sheets	as nece	ssary)	Group Art Unit	2811
	·			Examiner Name	S. Crane
Sheet	1	of	2	Attorney Docket Number	0756-2131

			U.S. PATENT DOCUMEN	TS	
Examiner Initials	Cite No.1	U.S. Patent Document	Name of Patentee or Applicant of	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code (if known)	2 Cited Document		
SWL		5,940,690	Kusumoto et al.	08/17/1999	
		6,337,232	Kusumoto et al.	01/08/2002	
		6,541,795	Kusumoto et al.	04/01/2003	
<del></del>		5,888,857	Zhang et al.	03/30/1999	
		6,323,071	Zhang et al.	11/27/2001	,
_/_		6,338,991	Zhang et al.	01/15/2002	
-		6,413,805	Zhang et al.	07/02/2002	
		6,071,764	Zhang et al.	06/06/2000	
$\neg \uparrow $		6,077,758	Zhang et al.	06/20/2000	
	<b> </b>	6,455,401	Zhang et al.	09/24/2002	'
-t		2002/0025659	Yamazaki et al.	02/28/2002	
	1	2002/0048891	Yamazaki et al.	04/25/2002	
<del></del>		6,423,586	Yamazaki et al.	07/23/2002	
	1	6,194,254	Takemura	02/27/2001	
Suju	<del> </del>	6,482,686	Takemura	11/19/2002	

			FC	REIGN PATENT DOC	UMENTS		,
Examiner Initiats	Cite No.1	F	oreign Patent Document	Name of Patentee or	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages	<b>⊤</b> ⁴
		Office <sup>3</sup>	Kind Code <sup>a</sup> Number <sup>4</sup> (# known)	Applicant of Cited Document	MM-OD-YYYY	or Relevant Figures Appear	·
Suj		JP	07-335906		12/22/1995		Abst. & U.S. Equiv.
		JP	07-045519		02/14/1995		Abst. & U.S. Equiv.
		JP	07-231100		08/29/1995		Abst. & U.S. Equiv.
		JP	07-094757		04/07/1995		Abst. & U.S. Equiv.
<del>)</del>		JP	07-192998		07/28/1995		Abst.
54 C		JP	05-299339	·	11/12/1993		Abst. & U.S. Equiv.

Examiner Signature	CRANC	Date Considered	5	17005
Signature	<u> </u>			

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Approved for use through 10/31/2002. OMB 0651-0031 U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitut	e for form 14	149A/PTO			Complete if Known			
INEO	DRAATI	ON DISC	OCHDE	Application Number	09/535	015		
•				Filing Date	March	1 24, 2000		
SIA	IEMEN	T BY APP	LICANI	First Named Inventor	Shunp	ei YAMAZAKI et al.		
	(use as man	y sheets as nece	essary)	Group Art Unit	2811			
				Examiner Name	S. Cra	ne		
Sheet	neet 2 of 2 .			Attorney Docket Number	0756-2	2131		
		·	1	U.S. PATENT DOCUMENT	S			
	Cita	U.S. Patent D	ocument		Date of Publication of Cited	Pages, Columns, Lines, When		

	1	U.S. Patent C	lea meet		Date of Publication of Cited	Pages, Columns, Lines, Where
Examiner Initials	Cite No.1	U.S. Faterit Document		Name of Patentee or Applicant of	Document	Relevant Passages or Relevant
	140.	Number	Kind Code <sup>2</sup> (if known)	Cited Document	MM-DD-YYYY	Figures Appear
SWL		6,162,704		Yamazaki et al.	12/19/2000	
(		6,294,441		Yamazaki	09/25/2001	
)		6,461,943		Yamazaki et al.	10/08/2002	
SWC		6,620,711		Yamazaki	09/16/2003	

				FOREIGN PATENT DO	CUMENTS	,	,
Examiner Initials	Cite No.1	Office <sup>3</sup>	Foreign Patent Document  Kind Code <sup>3</sup> Number <sup>4</sup> (If known)	Name of Patentée or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
SW(		JP	07-066425		03/10/1995		Abst. & U.S. Equiv.
7		JP	08-045839		02/16/1996		Abst. & U.S. Equiv.
		JР	08-045840		02/16/1996		Abst. & U.S. Equiv.
		JP	08-097169		04/12/1996	·	Abst. & U.S. Equiv.
ruk		KR	96-005879		02/23/1996		U.S. Equiv.
1			OTHER PRIC	R ART - NON PATENT LIT	ERATURE DOCUMENTS		
Examiner Initials	Cite No.1		Include name of the au item (book, magazine, joi	thor (in CAPITAL LETTERS) urnal, serial, symposium, cat publisher, city and/or cou	), title of the article (when app alog, etc.)., date, page(s), voluntry where published.	ropriate), title of the ume-Issue number(s),	T²
		T					

Examiner Signature	CRANG	Date Considered	5	7.00	

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Approved for use through 10/31/2002. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE
Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE				Complete if Known		
			OSLIDE	Application Number	09/535,015	
				Filing Date	March 24, 2000	
STATEMENT BY APPLICANT		First Named Inventor	Shunpei YAMAZAKI et al.			
(use as many sheets as necessary)			ssary)	Group Art Unit	2811	
				Examiner Name	S. Crane	
Sheet	1	of	1	Attorney Docket Number	0756-2131	

U.S. PATENT DOCUMENTS							
Cite No.1	U.S. Patent Document	Name of Patentee or Applicant of	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
	Number Kind Cod (if known)	9"					
	5,132,754	Serikawa et al.	07/21/1992				
	·						
ļ							
			<u> </u>				
<u> </u>			-				
ļ	ļ			·			
<b>_</b>			-				
	Cite No.1	No."  Number Kind Code (if known)  5,132,754	Number Kind Code <sup>2</sup> (if known)  Serikawa et al.	Number Kind Code <sup>2</sup> (if known)  Serikawa et al.  O7/21/1992			

FOREIGN PATENT DOCUMENTS								
Examiner Cite trittels No. 1	Cite No.1	Fo	reign Patent Docum	ment	Name of Patentee or	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	τ•
		Office <sup>3</sup>		d Code <sup>a</sup> f known)	Applicant of Cited Document			
								<u> </u>
						<u> </u>		
								<u></u>

Examiner Signature	CRANG	Date Considered	2007

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MREP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.